Third Semester B.E. Degree Examination, Dec.2017/Jan.2018

Analog Electronic Circuits

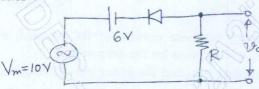
Time: 3 hrs.

Max. Marks: 100

Note: Answer FIVE full questions, selecting at least TWO questions from each part.

PART - A

- 1 a. Using Shockley's equation, determine the diode current at 25°C for a silicon diode with $I_S = 20$ pA and $V_D = 0.7$ V. Find the same when $V_D = 0.5$ V. (04 Marks)
 - b. Sketch the output waveform for the following circuit shown in Fig. Q1 (b), and plot the transfer characteristics (06 Marks)



c. Check the condition for the following circuit shown in Fig. Q1 (c) to work as clamper. Sketch the output waveform.

(05 Marks)

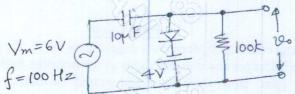
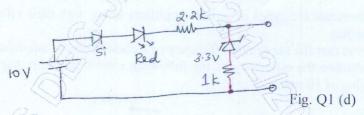


Fig. Q1 (c)

d. Find the current in the loop, the output voltage, and the power absorbed by each device.

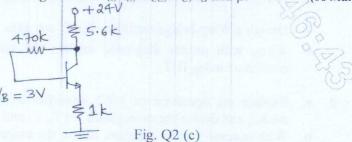
(05 Marks)



- 2 a. Derive the expression for I_B and V_{CE} of an emitter bias circuit. (04 Marks
 - b. Check the condition for the approximate analysis of the voltage-divider bias circuit and obtain the Q-point using approximate analysis, given: $V_{CC} = +12 \text{ V}$, $\beta = 120$, $R_{C} = 1.5 \text{ K}\Omega$, $R_{E} = 620 \Omega$, $R_{I} = 33 \text{ k}\Omega$ and $R_{I} = 4.7 \text{ k}\Omega$. Mark the Q-point on the DC load line.

(06 Marks)

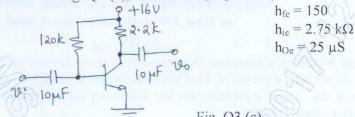
c. Determine the values for the following circuit: V_E , I_E , V_{CE} , V_C , I_B and β .



d. Design a fixed bias circuit for $V_{CC} = 10 \text{ V}$, $\beta = 120$, $I_{C_Q} = 1.4 \text{ mA}$ and $V_{CE_Q} = 5 \text{ V}$.

(04 Marks)

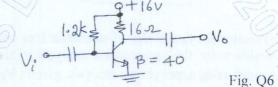
- 3 a Using r model, derive the expressions for Z_i, Z_o and A_V of a fixed bias circuit. (06 Marks)
 - b. Using exact analysis, determine Z_i , Z_o and A_V for the voltage-divider bias network if $R_1=220~k\Omega,~R_2=56~k\Omega,~R_C=6.8~k\Omega,~R_E=2.2~k\Omega,~\beta=180,~r_0=50~k\Omega$ and $V_{CC}=20V$.
 - c. For the network shown in Fig. Q3 (c), determine Z_i, Z_o and A_V- (04 Marks)



- 4 a. Explain the frequency response curves for RC-coupled, transformer-coupled and direct-coupled amplifiers, with reasons for the drop in gain. (09 Marks)
 - b. Determine the mid-band gain and the lower cut-off frequencies f_{L_s} and f_{L_c} for the voltage-divider bias BJT amplifier with $C_s=10\,\mu\text{F}$, $C_c=10\,\mu\text{F}$, $R_s=1\,\text{k}\Omega$, $R_1=36\,\text{k}\Omega$, $R_2=8.2\,\text{k}\Omega$, $R_E=1.5\,\text{k}\Omega$, $R_C=4.7\,\text{k}\Omega$, $R_L=2.2\,\text{k}\Omega$, $R_L=2.00\,\text{k}\Omega$ and $R_L=2.00\,\text{k}\Omega$. (11 Marks)

PART - B

- 5 a. For a Darlington connection, derive the expressions for Z_i, Z_o, A_i and A_V. (12 Marks)
 - b. Mention the advantages and disadvantages of the negative feedback. (04 Marks)
 - c. Calculate the gain, input impedance and output impedance of a voltage-series-feedback amplifier having A = -300, $R_i = 1.5 \text{ k}\Omega$, $R_0 = 50 \text{ k}\Omega$ and $\beta = -\frac{1}{15}$. (04 Marks)
- 6 a. Enumerate the types of power amplifiers along with their efficiency, conduction angle and Q-point. (05 Marks)
 - b. Prove that the maximum efficiency of a class-B power amplifier is 78.5%. (05 Marks)
 - c. Calculate the efficiency of the following circuit shown in Fig. Q6 (c), for an input current swing of 10 mA. (05 Marks)



- d. Along with the circuit diagram, explain the working of Class-C amplifier. (05 Marks)
- 7 a. Along with the circuit diagram, explain the working of a BJT phase-shift oscillator.
 - b. Design a Wien-bridge oscillator for $f_0 = 6$ kHz, making suitable assumptions. (06 Marks)
 - c. Along with proper diagrams, explain the series resonant and parallel resonant crystal oscillators using BJT. (68 Marks)
- 8 a. Explain the operation of JFET amplifier using fixed bias. Draw the JFET small signal model, and derive the expressions for Z_i , Z_o and A_V . (10 Marks)
 - b. With necessary circit diagram, obtain the expressions for Z_i, Z_o and A_V for an E-MOSFET voltage-divider configuration. (10 Marks)

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